Analysis of Organic Solvent Samples by Automatic Standard Addition Method using ASAS-ICP-MS/MS

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Trusted Answers

Introduction

- Elemental analysis of process chemicals at ultra-trace levels (ng/L; ppt) is a vital application to ensure the yield and operational reliability of semiconductor devices.
- Isopropyl alcohol (IPA) is used to remove organic and metallic residues and impurities from the surface of silicon wafers.
- Since IPA comes into direct contact with the wafer surface, it is necessary to control the concentration of trace metals present in the organic solvent.
- SEMI standard C41-0705 specifies a maximum contaminant level of less than 100 ppt for each element in high purity grade 4 IPA [1].
- Advanced analytical skills are required for the application. •

In this study, impurities in IPA were quantified by Method of Standard Addition (MSA) using an Automatic Standard Addition System (ASAS) (IAS Inc. Japan) and triple quadrupole ICP-MS (ICP-MS/MS).

The method allows the quantification of ultra-trace level impurities in IPA regardless of the skill level of the analyst.

Experimental

Automated Standard Addition System (ASAS)

The operation of the IAS Automated Standard Addition System (ASAS) is described in the working example and in Figure 2.

2. IAS Inc

Working example: How to add a 50 ppt spike to the sample?

- Prepare a 1 ppb standard stock solution for MSA.
- When the autosampler probe moves to one of the vials, it triggers the automatic measurement of the sample uptake rate using two flow sensors.
- An air bubble is introduced from the valve labeled "Air Valve".
- Optical fiber sensors then measure the time it takes for the air bubble to pass from Sensor 1 to Sensor 2. (The flow rate will be approximately 200 μ L/min in self-aspiration mode).
- The ASAS software automatically calculates the flow rate of the 1 ppb stock standard required to achieve the 50 ppt spike level
- The standard will be introduced to the sample via the "Mix Block" at the calculated flow rate by the syringe pump.

Results and Discussion



Experimental

Reagents and samples

- Sample: distilled IPA (Electronic Grade).
- Standard stock solution for MSA: a 1 μ g/L (ppb) mixed multi-element standard solution was prepared by diluting a 10 ppm mixed multi-element standard solution :XSTC-7, XSTC-8 and XSTC-331(SPEX CertiPrep, NJ, US) with distilled IPA. Nitric acid (68% ultrapure HNO₃ (TAMAPURE-AA-10)) was added to 1% to stabilize the spiked elements in the IPA sample.
- The stock solution was loaded on the ASAS.
- All target concentration solutions required for the analysis were automatically prepared by the ASAS.
- All preparation and analysis steps were performed in a Class 10,000 clean room.

Instrumentation

- Standard Agilent 8900 Semiconductor configuration ICP-MS/MS instrument with s-lens equipped with:
 - A glass coaxial nebulizer.
 - Peltier cooled quartz spray chamber
 - Quartz torch (1.5 mm id)
 - Platinum-tipped sampling and skimmer cones

Tuning conditions are shown in Table 1, other acquisition parameters are shown in Table 2. A photo of the ASAS fitted to the ICP-MS/MS is shown in Figure 1.

Table 1. ICP-MS/MS operating conditions.

In this example, introducing a 1 ppb stock standard solution at $10.0 \,\mu$ L/min would equate to spiking the sample at the 50 ppt concentration level.

The syringe pump delivers the standard solution from the loop into the sample line via the "Mix Block". The appropriate flow rate is calculated automatically, as explained in the working example. The MSA solution is then introduced into the plasma of the ICP-MS using a nebulizer operating in selfaspiration mode.



Figure 3. MSA calibration curves for ²⁴Mg, ²⁷Al, ⁵²Cr, ³¹P.

Table 4. DLs and BECs in IPA. Analytes shown in bold are SEMI grade 4 elements.

Analyte	Q1	Q2	Tune Mode	DL (ng/L)	BEC	20 ng/L Recovery(%)
	7	7				
LI Ro	/	/			0.040	99
De D	9	9	No gas	0.023	10.000	99
D			INO Yas	<u> </u>		90
INA	23	23	NH ₃	0.060	0.97	109
Mg	24	24	NH ₃	0.020	0.082	102
AI	27	27	NH ₃	0.042	0.16	100
Р	31	4/	O ₂ He	2.6	43	99
K	39	39	NH ₃	1.6	2./	10/
Ca	40	40	NH ₃	0.19	0.62	108
Ti	48	64	O ₂ He	0.23	1.3	99
V	51	67	O ₂ He	0.020	0.030	99
Cr	52	52	NH ₃	0.16	0.48	92
Mn	55	55	NH ₃	0.030	0.030	102
Fe	56	56	NH ₃	0.16	1.1	101
Со	59	59	Не	0.020	0.020	99
Ni	60	60	He	0.43	0.80	101
Cu	63	63	O ₂ He	0.38	6.4	97
Zn	64	64	He	0.71	0.72	98
Ga	71	71	O ₂ He	0.013	0.005	100
Ge	74	74	He	0.30	0.070	96
As	75	91	O ₂ He	0.00	0.26	108
Sr	88	88	O_2 He	0.005	0.002	98
7r	90	106	O_2 He	0.000	0.002	90
Nh	93	93	$H_{\rm e}$ (MG0.5)	0.000	0.020	102
Mo	90	120	$\bigcap_{n \in H^{\infty}} H^{n}$	0.14	0.41	102
	101	100			0.11	
Dh	101	101			0.00	99
	105	105			0.10	100
Pu	103	103		0.070	0.040	100
Ay	10/	107		0.014	0.000	97
			O_2 He	0.035	0.004	98
In	115	115	O_2 He	0.012	0.008	99
Sn	118	118	O ₂ He	0.058	0.034	100
Sb	121	121	O ₂ He	0.056	0.009	103
Те	125	125	O ₂ He	0.78	0.29	97
Cs	133	133	H ₂ (MG0.8)	0.060	0.022	96
Ba	138	138	O ₂ He	0.009	0.004	99
Hf	178	178	He	0.000	0.000	105
Та	181	213	O ₂ He	0.033	0.009	96
W	182	214	O ₂ He	0.21	0.049	97
Re	185	185	O ₂ He	0.000	0.000	96
lr	193	193	No gas	0.060	0.006	101
Pt	195	195	O ₂ He	0.51	0.45	100
Au	197	197	O ₂ He	0.063	0.007	110
TI	205	205	O ₂ He	0.029	0.015	99
Pb	208	208	O ₂ He	0.047	0.042	100
Bi	209	209	02 He	0.021	0.004	98
Th	232	248	O_2 He	0.11	0.027	97
	238	2.54	$O_{2} He$	0.18	0.022	91
U	238	254	U ₂ He	0.18	0.048	91

			-				
	H ₂ (MG0.8)	NH ₃	No gas	H ₂ (MG0.5)	Не	O ₂ He	
Scan type	MS/MS						
RF power (W)	1500						
Sampling depth (mm)	18						
Carrier gas flow rate (L/min)	0.70						
20% O ₂ Ar balance gas flow rate (L/min)	0.30 (30 % of full scale)						
Spray chamber temp (°C)	-5						
Makeup gas (MG) flow rate (L/min)	0.80	0.70		0.50			
He gas flow rate (mL/min)	_	1	_	_	5	12	
H ₂ gas flow rate (mL/min)	5	_	_	10	-	_	
NH₃gas flow rate (mL/min)	-	2.0 (20%)	-	_	-	_	
O ₂ gas flow rate (mL/min)	_	_	-	_	-	0.075 (5%)	
OctP bias (V)	-18	-5	-10	-30	-20	-3	
Axial acceleration (V)	-	1		0	-	1	
Energy discrimination (V)	0	-10	3	-10	3	-10	

Table 2. Acquisition parameters.

Parameter	Setting		
Q2 peak pattern	1 point		
Doplicator	3 (spiked solution)		
Replicates	10 (unspiked solution)		
Sweeps/replicate	10		
Integration time	Phosphorus: 10 sec,		
	all other elements: 1 sec		



Valve (IN)

Valve (OUT)

Figure 2. Operation of the ASAS.

Results and Discussion

DLs and BECs

- 48 elements were measured in IPA using the 8900 operating in multiple tune modes.
- Ouantitative results and DLs for SEMI and non-SEMI specified elements are shown in Table 4.
- Each detection limit was calculated as 3-sigma of 10 replicate measurements of a blank IPA sample.

Mg, Al, and Cr determination

Combining cool plasma with CRC technology is a powerful mode for interference removal [2].

In this study, a more robust warm plasma was used and a small amount of oxygen gas was mixed with argon gas to decompose the carbon matrix thus avoiding carbon deposition on the interface cones.

Because the major isotope of ²⁴Mg⁺ suffers an interference from ¹²Cr¹²C in organic samples, Mg was determined using a warm plasma with NH_3 cell gas.

- The calibration curve for ²⁴Mg shows that ¹²C¹²C⁺ interference was removed successfully.
- BEC for Mg: 0.082 ng/L (ppt).
- Conclusions
 - By providing a high degree of automation, the Agilent 8900 ICPMS/MS fitted with IAS's ASAS auto-MSA system



Figure 1. ASAS-ICP-MS/MS.

DL for Mg: 0.020 ppt (Table 3).

The same approach was effective for the determination of other interfered elements such as ²⁷Al and ⁵²Cr.

P determination

In this study, the same measurement conditions proposed by Mizobuchi et al were used for P (He+ O_2 mode) [4].

- The calibration curve in Figure 3 shows good linearity from 5 to 50 ppt for P.
- BEC for P: 43 ng/L (ppt).
- DL for P: 2.6 ppt (Table 3).

Table 3. Main interferences in organic solvents.

Analyte	Interferences	DL (ng/L)	BEC (ng/L)
²⁴ Mg	$^{12}Cr^{12}C^{+}$	0.020	0.082
²⁷ Al	¹² C ¹⁵ N ⁺ , ¹³ C ¹⁴ N ⁺ , ¹² C ¹⁴ N ¹ H ⁺ [3]	0.042	0.16
⁵² Cr	$^{40}Ar^{12}C^{+}$	0.16	0.48
³¹ P	¹⁵ N ¹⁶ O ⁺ , ¹⁴ N ¹⁷ O ⁺ , ¹³ C ¹⁸ O ⁺	2.6	43

simplifies the elemental analysis of semiconductor process chemicals.

- Eliminating manual tasks during ultratrace analysis lowers the risk of contamination. Limiting the handling of reagents and samples also reduces the likelihood of errors arising during the experimental procedure, leading to an increased confidence in the data quality.
- The elements specified in SEMI C41-0705, including P were measured at sub-ppt to ppt levels in IPA. The results exceed current SEMI specifications for IPA.

References

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